

**WBFBP-02C Plastic-Encapsulate Diodes****DTESDB5V0LED02** ESD Protection Diode**DESCRIPTION**

The DTESDB5V0LED02 is designed to protect voltage sensitive components from ESD. Excellent clamping capability, low leakage, and fast response time provide best in class protection on designs that are exposed to ESD. Because of its small size, it is suited for use in cellular phones, MP3 players, digital cameras and many other portable applications where board space is at a premium.

**WBFBP-02C**

(1.0×0.6×0.5)

unit: mm

**FEATURES**

- Stand-off Voltage: 5.0 V
- Low Leakage
- Response Time is Typically < 1 ns
- ESD Rating of Class 3 (> 16 kV) Per Human Body Model
- IEC61000-4-2 Level 4 ESD Protection
- IEC61000-4-4 Level 4 EFT Protection
- This is a Pb-Free Device

**MARKING: EB****Maximum Ratings @Ta=25°C**

Parameter	Symbol	Limit	Unit
IEC61000-4-2(ESD) Air Contact		±30 ±30	KV
ESD Voltage Per Human Body Model		16	KV
Per Machine Model		400	V
Total Power Dissipation on FR-5 Board (Note 1)	<b>P<sub>D</sub></b>	100	mW
Thermal Resistance Junction-to-Ambient	<b>R<sub>ΘJA</sub></b>	1250	°C/W
Lead Solder Temperature – Maximum (10 Second Duration)	<b>T<sub>L</sub></b>	260	°C
Junction and Storage Temperature Range	<b>T<sub>j</sub>, T<sub>stg</sub></b>	-55 ~ +150	°C

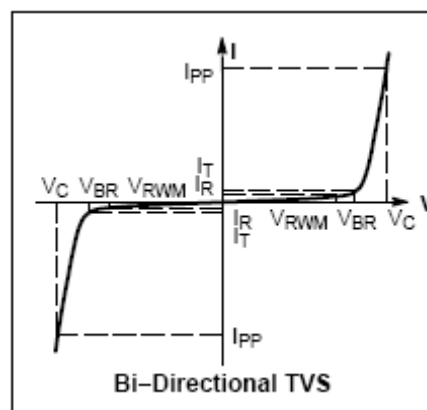
Stresses exceeding maximum ratings may damage the device. Maximum Ratings are stress ratings only.

Functional operation above the recommended. Operating conditions is not implied. Extended exposure to stresses above the recommended operating conditions may affect device reliability.

1. FR-5 = 1.0 x 0.75 x 0.62 in.

# **ELECTRICAL CHARACTERISTICS** (Ta = 25°C unless otherwise noted)

Symbol	Parameter
$I_{PP}$	Maximum Reverse Peak Pulse Current
$V_C$	Clamping Voltage @ $I_{PP}$
$V_{RWM}$	Working Peak Reverse Voltage
$I_R$	Maximum Reverse Leakage Current @ $V_{RWM}$
$V_{BR}$	Breakdown Voltage @ $I_T$
$I_T$	Test Current
C	Max. Capacitance @ $V_R=0$ and $f=1\text{MHz}$



## **ELECTRICAL CHARACTERISTICS** (Ta = 25°C unless otherwise noted)

Device	Device Marking	$V_{RWM}$ (V)	$I_R$ ( $\mu\text{A}$ ) @ $V_{RWM}$	$V_{BR}$ (V) @ $I_T$ (Note 2)		$I_T$ mA	$V_C$ @ $I_{PP} = 5\text{A}$	$I_{PP}$ (A)	$V_C$ (V) @ Max $I_{PP}$	C (pF)
		Max	Max	Min	Max		V	Max	Max	Max
DTESDB5V0LED02	EB	5.0	1.0	5.8	8.8	1.0	10	11.2	12.5	30

2.  $V_{BR}$  is measured with a pulse test current  $I_T$  at an ambient temperature of 25°C.